

IN THE CLAIMS

Please cancel claims 1-24 without prejudice. Claims 28-38 are new in the present application.

25. (Original) A method of forming a transistor comprising:
- forming a gate dielectric layer on a layer of semiconductor material;
 - forming a gate electrode on the gate dielectric layer;
 - implanting dopants into the layer of semiconductor material to form doped tip regions in the layer with a channel between the tip regions;
 - etching the layer to form source and drain recesses in the layer with the tip regions between the recesses; and
 - filling the source and drain recesses with a source and a drain respectively.
26. (Original) The method of claim 25 wherein at least one of the source and the drain is made of a film material which:
- (a) includes a dopant selected from one of a p-dopant and an n-dopant; and
 - (b) is formed epitaxially on the semiconductor materials.
27. (Original) The method of claim 25 wherein the source and drain have a depth into the layer and are spaced by a width from one another, a ratio of the depth to the width being at least 0.12.

28. (New) The method of claim 26, wherein the semiconductor material has a first lattice with a first spacing and the film material has a second lattice having a second structure which is the same as the first structure, the second lattice having a second spacing which differs from the first spacing.

29. (New) The method of claim 28, wherein:

(a) if the dopant is a p-dopant, the second spacing is larger than the first spacing; and

(b) if the dopant is an n-dopant, the second spacing is smaller than the first spacing.

30. (New) The method of claim 28, wherein the difference between the first spacing and the second spacing creates a stress in the channel.

31. (New) The method of claim 28, wherein the second material includes the semiconductor material and an additive, the difference between the first spacing and the second spacing being due to the additive.

32. (New) The method of claim 31, wherein the semiconductor material is silicon and the additive is selected from one of germanium and carbon.

33. (New) The method of claim 32, wherein the additive is germanium.

34. (New) The method of claim 33, wherein the germanium comprises between 1 and 20 atomic percent of the silicon and the germanium of the film material.

35. (New) The method of claim 26, wherein:

(a) if the dopant of the film material is a p-dopant, the dopants of the tip regions are p-dopants; and

(b) if the dopant of the film material is an n-dopant, the dopants of the tip regions are n-dopants.

36. (New) The method of claim 26, wherein the dopant comprises at least $0.5 \times 10^{20} / \text{cm}^3$ of the film material.

37. (New) The method of claim 36, wherein the film material has a resistivity of less than 1.1mOhm-cm.

38. (New) The method of claim 25, wherein the gate dielectric layer is formed before the dopants are implanted.